

PMZB350UPE

20 V, single P-channel Trench MOSFET 1 August 2012

Product data sheet

1. **Product profile**

1.1 General description

P-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1006B-3 (SOT883B) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Low threshold voltage
- Very fast switching
- Trench MOSFET technology
- 1.8 kV ESD protected

1.3 Applications

- Relay driver
- High-speed line driver
- High-side loadswitch
- Switching circuits

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	-20	V
V _{GS}	gate-source voltage			-8	-	8	V
I _D	drain current	$V_{GS} = -4.5 \text{ V}; T_{amb} = 25 \text{ °C}; t \le 5 \text{ s}$	[1]	-	-	-1.4	Α
Static characteristics							
R _{DSon}	drain-source on-state resistance	V_{GS} = -4.5 V; I_D = -0.3 A; T_j = 25 °C		-	330	450	mΩ

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².



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2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	1 🔲	D I
2	S	source	2 3	
3	D	drain	Transparent top view DFN1006B-3 (SOT883B)	G S 017aaa259

3. Ordering information

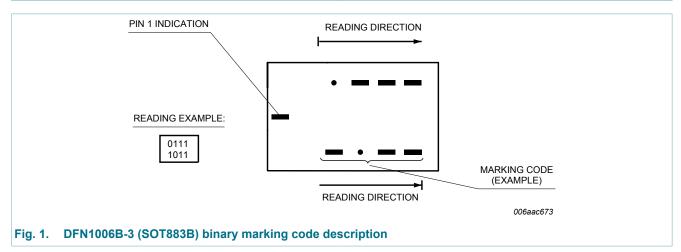
Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PMZB350UPE	DFN1006B-3	Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.37 mm	SOT883B		

4. Marking

Table 4. Marking codes

Type number	Marking code
PMZB350UPE	0100 1100



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5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-20	V
V _{GS}	gate-source voltage			-8	8	V
I _D	drain current	$V_{GS} = -4.5 \text{ V}; T_{amb} = 25 \text{ °C}; t \le 5 \text{ s}$	[1]	-	-1.4	Α
		V _{GS} = -4.5 V; T _{amb} = 25 °C	[1]	-	-1	Α
		V _{GS} = -4.5 V; T _{amb} = 100 °C	[1]	-	-0.7	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-2.8	Α
P _{tot} total powe	total power dissipation	T _{amb} = 25 °C	<u>[2]</u>	-	360	mW
			[1]	-	715	mW
		T _{sp} = 25 °C		-	3125	mW
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain of	diode		'		'	,
I _S	source current	T _{amb} = 25 °C	[1]	-	-0.8	Α
ESD maximum	n rating					-
V _{ESD}	electrostatic discharge voltage	НВМ	[3]	-	1800	V

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm²

^[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

^[3] Measured between all pins.

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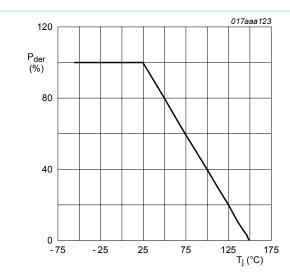


Fig. 2. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

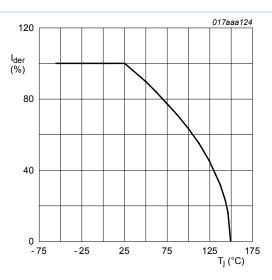


Fig. 3. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

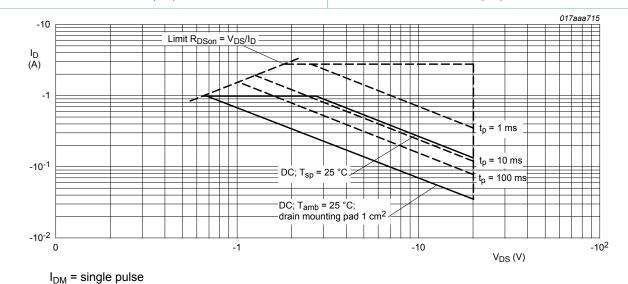


Fig. 4. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance	in free air	[1]	-	304	350	K/W
from junction to ambient		[2]	-	150	175	K/W	
		[3]	-	90	103	K/W	

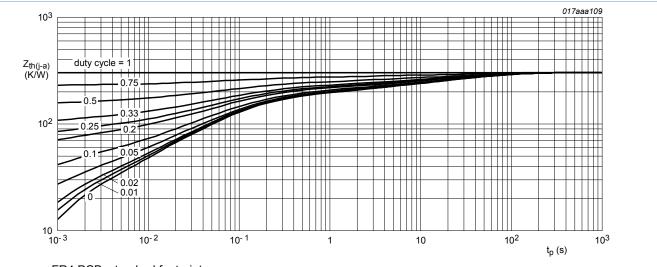
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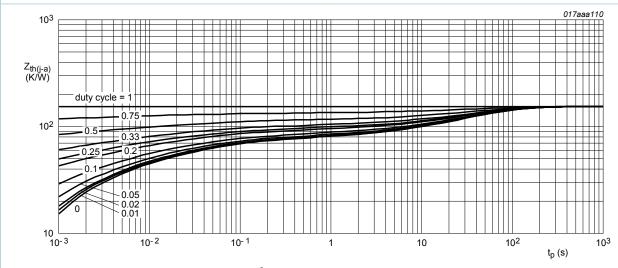
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-sp)}	thermal resistance from junction to solder point		-	35	40	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm 2 , t \leq 5 s.



FR4 PCB, standard footprint

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 1 cm²

Fig. 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = -250 μ A; V_{GS} = 0 V; T_j = 25 °C	-20	-	-	V
V_{GSth}	gate-source threshold voltage	I_D = -250 μ A; V_{DS} = V_{GS} ; T_j = 25 °C	-0.45	-0.7	-0.95	V
drain leakage cur	drain leakage current	V _{DS} = -20 V; V _{GS} = 0 V; T _j = 25 °C	-	-	-1	μA
		V _{DS} = -20 V; V _{GS} = 0 V; T _j = 150 °C	-	-	-10	μΑ
I _{GSS}	gate leakage current	V _{GS} = -8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μΑ
	V _{GS} = 8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	10	μΑ	
R _{DSon}	drain-source on-state	V_{GS} = -4.5 V; I_D = -0.3 A; T_j = 25 °C	-	330	450	mΩ
resistance	resistance	V _{GS} = -4.5 V; I _D = -0.3 A; T _j = 150 °C	-	478	645	mΩ
		V _{GS} = -2.5 V; I _D = -0.2 A; T _j = 25 °C	-	420	645	mΩ
		V _{GS} = -1.8 V; I _D = -0.1 A; T _j = 25 °C	-	520	940	mΩ
9 _{fs}	forward transconductance	V_{DS} = -10 V; I_D = -0.3 A; T_j = 25 °C	-	1.4	-	S
Dynamic cl	haracteristics					
Q _{G(tot)}	total gate charge	V_{DS} = -10 V; I_{D} = -0.3 A; V_{GS} = -4.5 V;	-	1.3	1.9	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	0.2	-	nC
Q_{GD}	gate-drain charge		-	0.25	-	nC
C _{iss}	input capacitance	V _{DS} = -10 V; f = 1 MHz; V _{GS} = 0 V;	-	127	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	34	-	pF
C _{rss}	reverse transfer capacitance		-	25	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = -10 V; I_{D} = -0.3 A; V_{GS} = -4.5 V;	-	4	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega$; $T_j = 25 °C$	-	5	-	ns
t _{d(off)}	turn-off delay time		-	26	-	ns
t _f	fall time		-	9	-	ns
Source-dra	in diode		ı	'	1	
V_{SD}	source-drain voltage	I _S = -0.1 A; V _{GS} = 0 V; T _i = 25 °C	-	-0.7	-1.2	V

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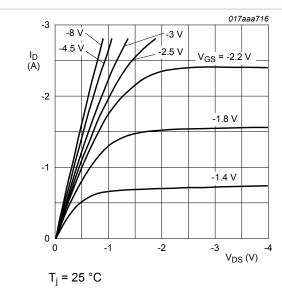


Fig. 7. Output characteristics: drain current as a function of drain-source voltage; typical values

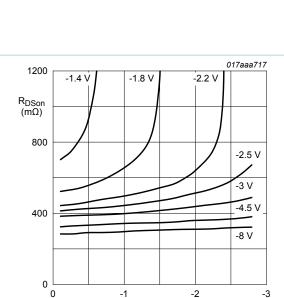
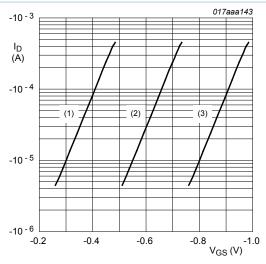


Fig. 9. Drain-source on-state resistance as a function of drain current; typical values

T_i = 25 °C

 $I_D(A)$



$$T_i$$
 = 25 °C; V_{DS} = -3 V

- (1) minimum values
- (2) typical values
- (3) maximum values

Fig. 8. Sub-threshold drain current as a function of gate-source voltage

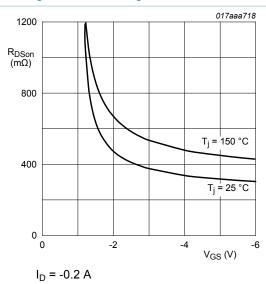


Fig. 10. Drain-source on-state resistance as a function of gate-source voltage; typical values

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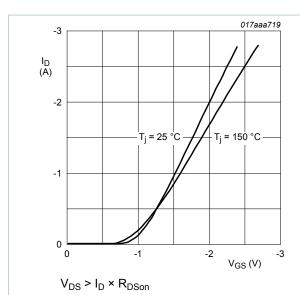


Fig. 11. Transfer characteristics: drain current as a function of gate-source voltage; typical values

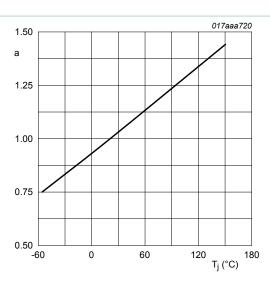


Fig. 12. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

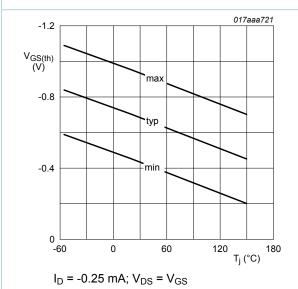


Fig. 13. Gate-source threshold voltage as a function of junction temperature

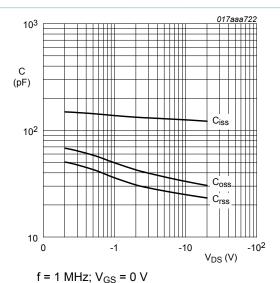
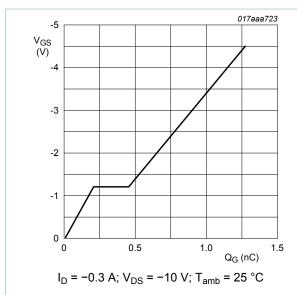


Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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V_{GS}(pl)
V_{GS}(th)
V_{GS}
Q_{GS1} Q_{GS2}
Q_{GS}
Q_G(tot)
017aaa137

Fig. 16. Gate charge waveform definitions

Fig. 15. Gate-source voltage as a function of gate charge; typical values

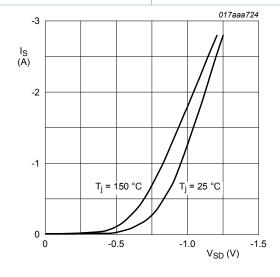
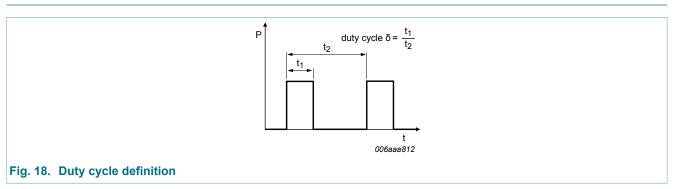


Fig. 17. Source current as a function of source-drain voltage; typical values

8. Test information

 $V_{GS} = 0 V$



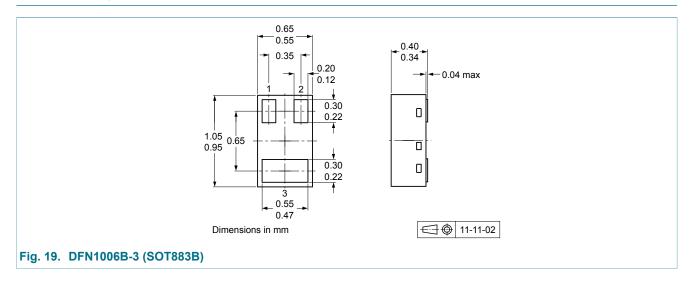
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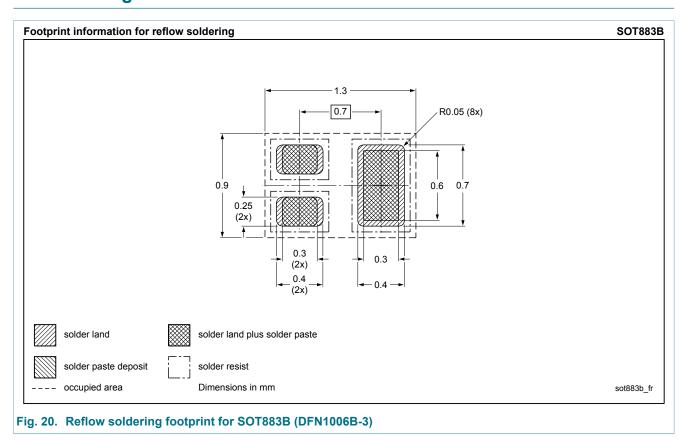
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9. Package outline



10. Soldering



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11. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMZB350UPE v.1	20120801	Product data sheet	-	-

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12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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